

# EVVOSEMI<sup>®</sup>

THINK CHANGE DO



ESD



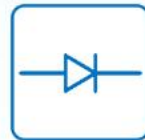
TVS



MOS



LDO



Diode



Sensor



DC-DC

## Product Specification

▶ Domestic	Part Number	2SC5386
▶ Overseas	Part Number	2SC5386
▶ Equivalent	Part Number	2SC5386

EV is the abbreviation of name EVVO

## Silicon NPN Power Transistors

### DESCRIPTION

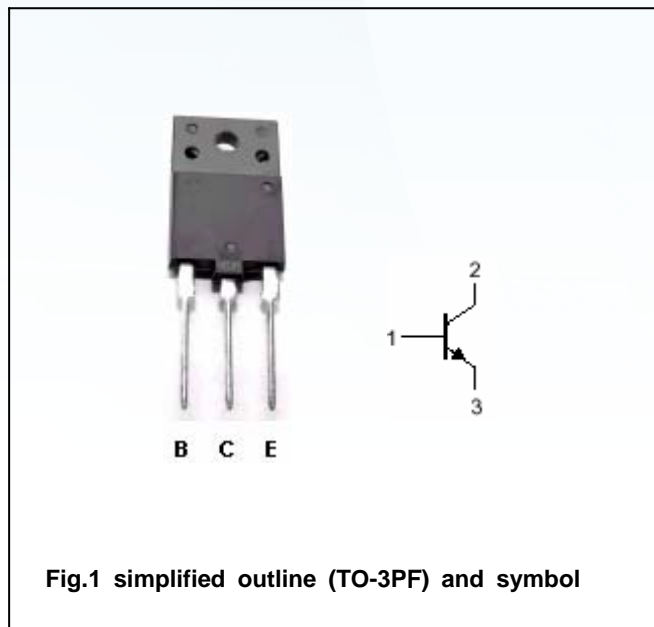
- With TO-3PF package
- High voltage;high speed
- Low collector saturation voltage

### APPLICATIONS

- Horizontal deflection output for high resolution display,color TV
- High speed switching applications

### PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



### Absolute maximum ratings(Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	600	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		8	A
I <sub>CM</sub>	Collector current-Peak		16	A
I <sub>B</sub>	Base current		4	A
P <sub>C</sub>	Total power dissipation	T <sub>C</sub> =25	50	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

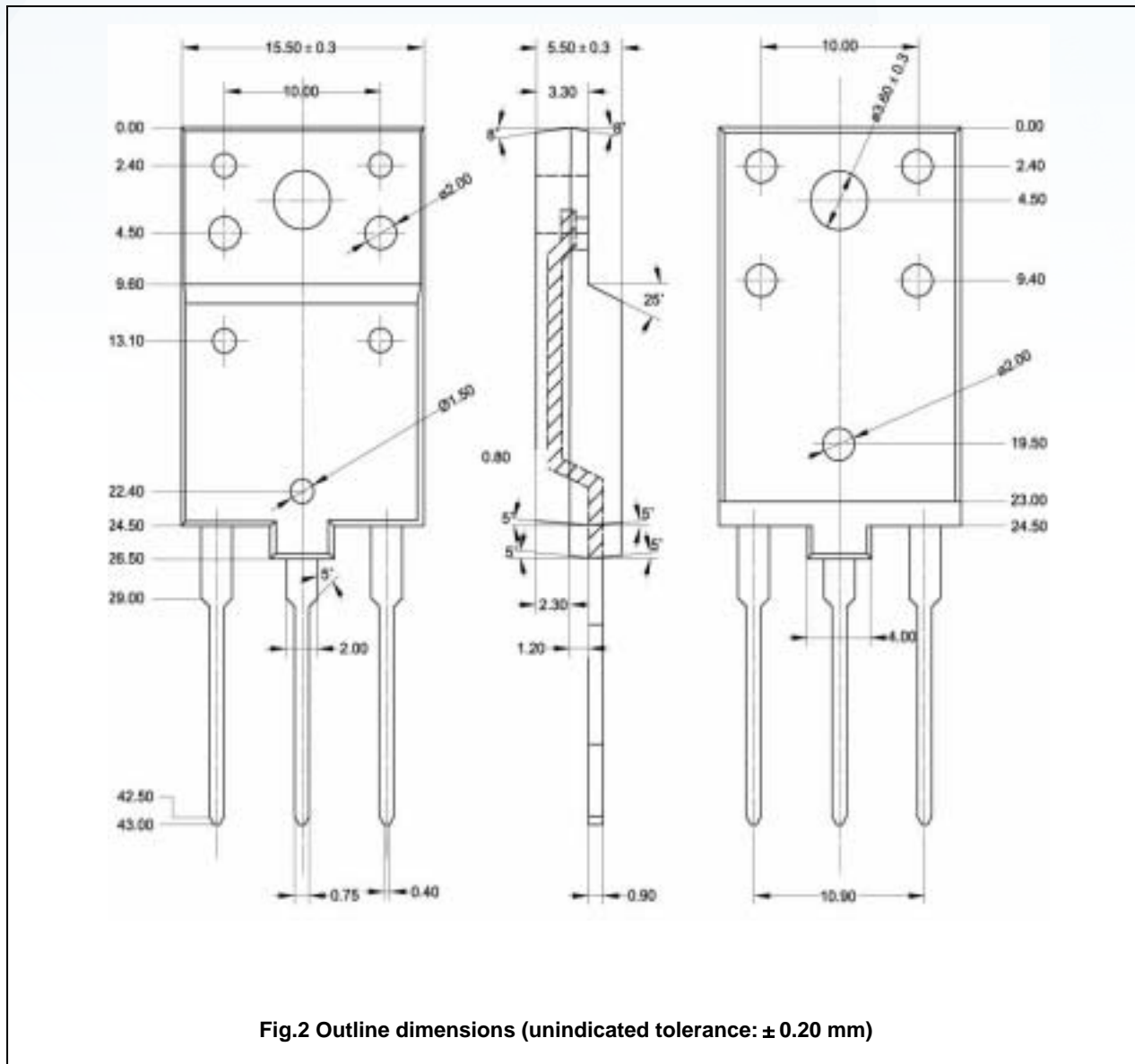
**CHARACTERISTICS**
**T<sub>j</sub>=25 unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	600			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =6A; I <sub>B</sub> =1.5A			3.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =6A; I <sub>B</sub> =1.5A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =1500V; I <sub>E</sub> =0			1.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	15		35	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =6A ; V <sub>CE</sub> =5V	4.3		7.5	
C <sub>ob</sub>	Collector output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V, f=1MHz		105		pF
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =0.1A ; V <sub>CE</sub> =10V		1.7		MHz

**Switching times**

t <sub>s</sub>	Storage time	I <sub>CP</sub> =5A; I <sub>B1(end)</sub> =1.0A f <sub>H</sub> =64kHz		2.5	3.5	μs
t <sub>f</sub>	Fall time			0.15	0.3	μs

## PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.20$  mm)

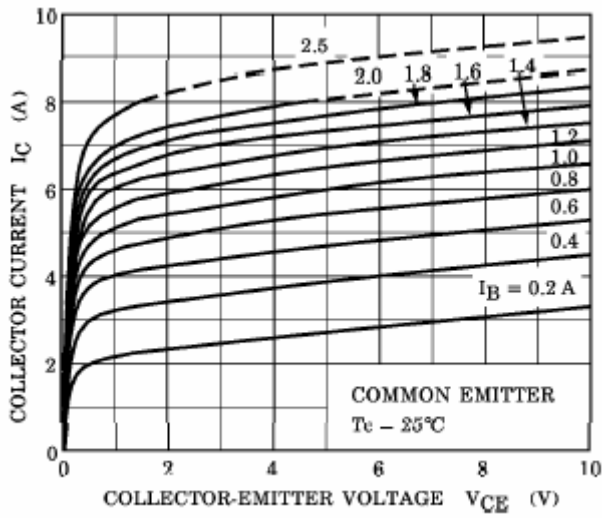


Fig.3 Static Characteristic

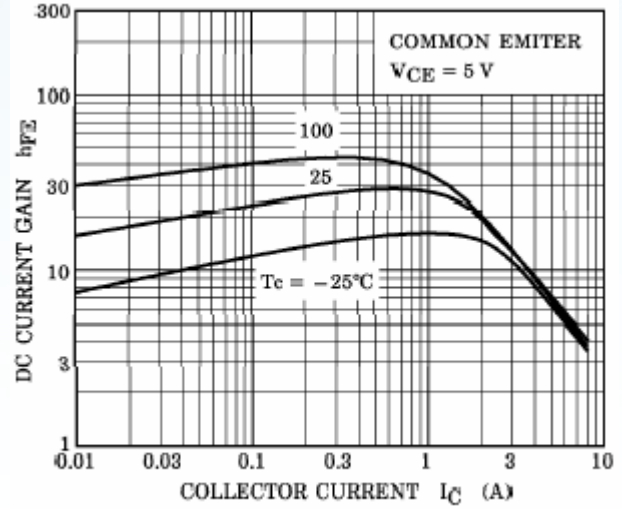


Fig.4 DC current Gain

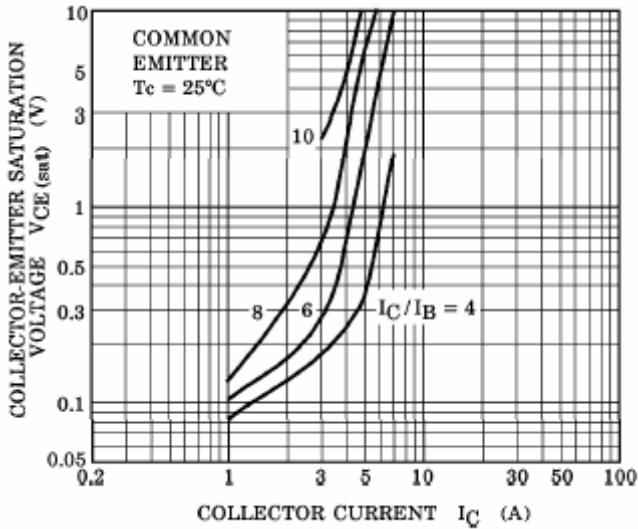


Fig.5 Collector-Emitter Saturation Voltage

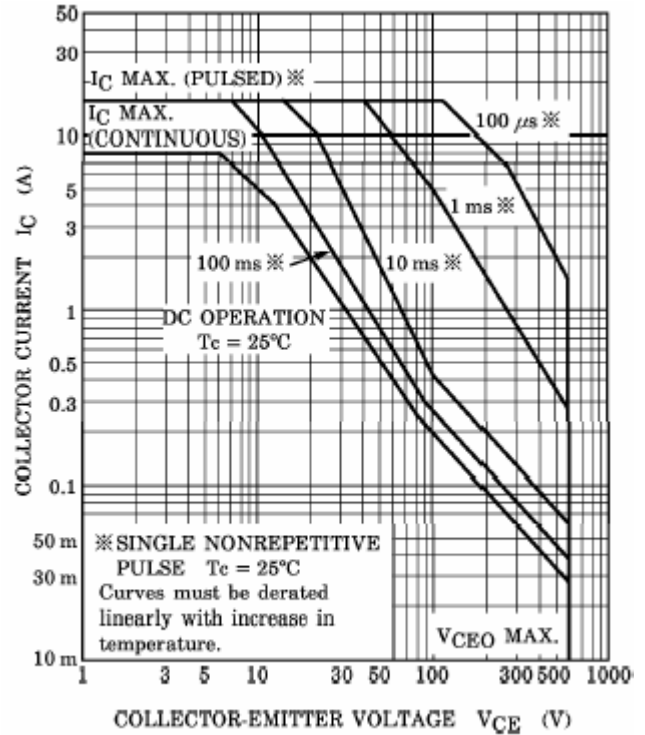


Fig.6 Safe Operating Area

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